

Silicon NPN Power Transistors

2N6259

DESCRIPTION

- With TO-3 package
- Low collector saturation voltage
- High power dissipation

APPLICATIONS

- Designed for high power audio ,disk head positioners,linear amplifiers,switching regulators solenoid drivers,and DC-DC converters or inverters

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

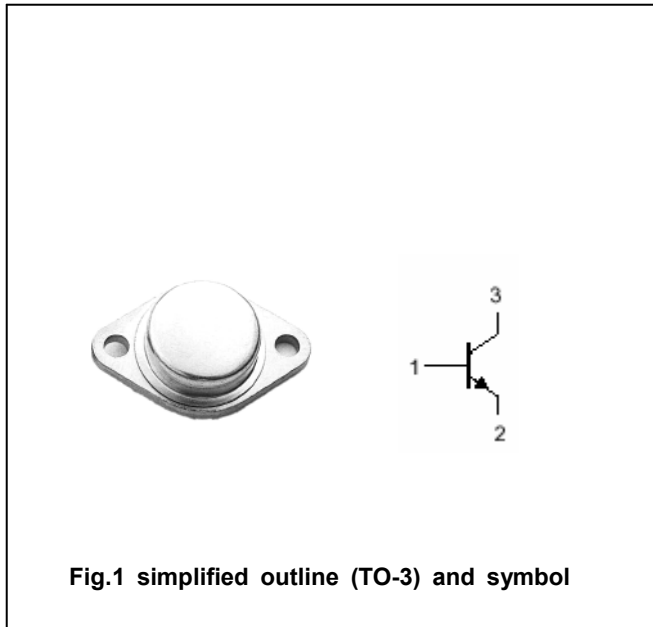


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	170	V
V _{CEO}	Collector-emitter voltage	Open base	150	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		16	A
I _{CM}	Collector current-peak		30	A
I _B	Base current		4	A
I _{BM}	Base current-peak		15	A
P _D	Total Power Dissipation	T _C =25□	150	W
T _j	Junction temperature		200	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.17	□/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	150			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =8A ; I _B =0.8A			1.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =16A ; I _B =3.2A			2.5	V
V _{BE}	Base-emitter on voltage	I _C =8A ; V _{CE} =2V			2.0	V
I _{CEO}	Collector cut-off current	V _{CE} =130V ; I _B =0			10	mA
I _{CEx}	Collector cut-off current	V _{CE} =150V ; V _{BE(off)} =1.5V			2.0	mA
I _{CBO}	Collector cut-off current	V _{CB} =150V ; I _E =0			2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V ; I _C =0			5.0	mA
h _{FE-1}	DC current gain	I _C =8A ; V _{CE} =2V	15		60	
h _{FE-2}	DC current gain	I _C =16A ; V _{CE} =4V	10			

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PACKAGE OUTLINE

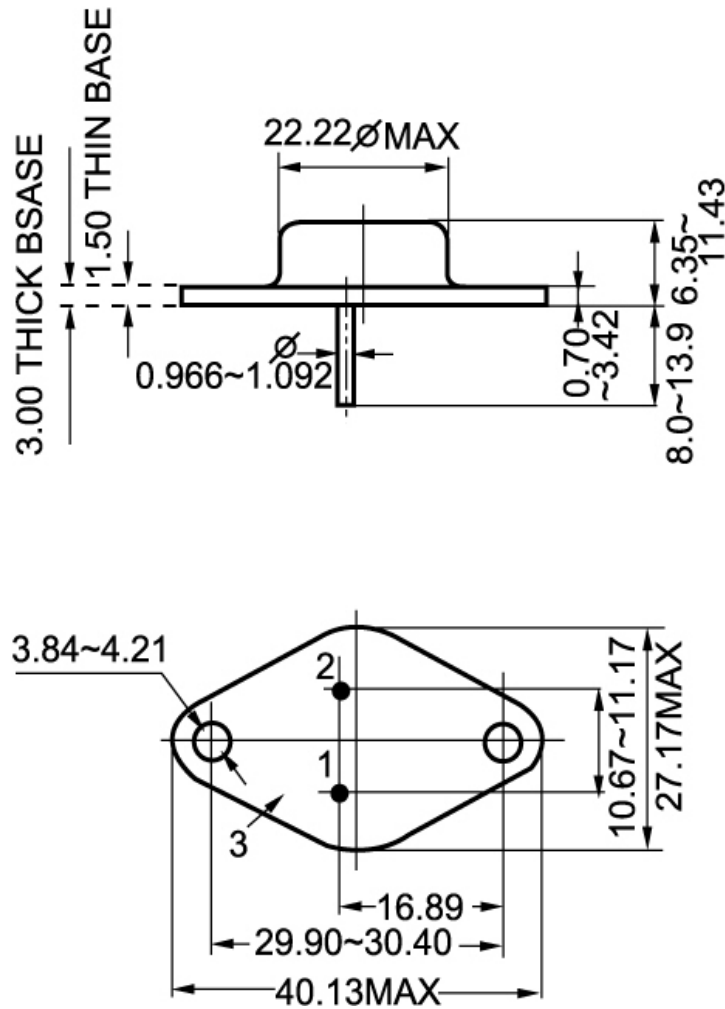


Fig.2 outline dimensions (unindicated tolerance:±0.10mm)